NDF03N60Z, NDD03N60Z

N-Channel Power MOSFET 600 V, 3.6 Ω

Features

- Low ON Resistance
- Low Gate Charge
- ESD Diode−Protected Gate
- 100% Avalanche Tested
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	NDF	NDD	Unit
Drain−to−Source Voltage	V_{DSS}	600		V
Continuous Drain Current $R_{\theta JC}$	I_D	3.1 (Note 1)	2.6	A
Continuous Drain Current $R_{\theta JC}$ T_A = 100°C	I_D	2.9 (Note 1)	1.65	A
Pulsed Drain Current, V_{GS} @ 10 V	I_{DM}	12	10	A
Power Dissipation $R_{\theta JC}$	P_D	27	61	W
Gate−to−Source Voltage	V_{GS}	±30		V
Single Pulse Avalanche Energy, I_D = 3.0 A	E_{AS}	100		mJ
ESD (HBM) (JESD 22−A114)	V_{esd}	3000		V
RMS Isolation Voltage (t = 0.3 sec., R.H. ≤ 30%, T_A = 25°C) (Figure 17)	V_{ISO}	4500		V
Peak Diode Recovery (Note 2)	dv/dt	4.5		V/ns
Continuous Source Current (Body Diode)	I_S	3.0		A
Maximum Temperature for Soldering Leads	T_L	260		°C
Operating Junction and Storage Temperature Range	T_J, T_{stg}	−55 to 150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

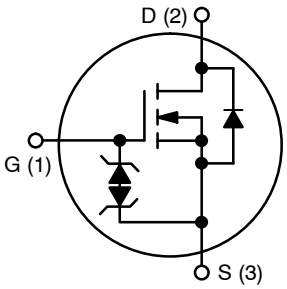
1. Limited by maximum junction temperature
2. I_{SD} = 3.0 A, di/dt ≤ 100 A/μs, V_{DD} ≤ BV_{DSS}, T_J = +150°C

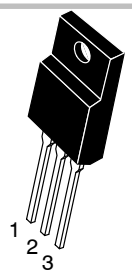
ON Semiconductor®

www.onsemi.com

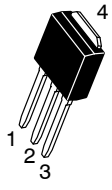
V_{DSS}	$R_{DS(on)}$ (MAX) @ 1.2 A
600 V	3.6 Ω

N−Channel

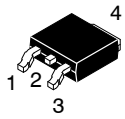




NDF03N60ZG,
NDF03N60ZH
TO−220FP
CASE 221AH



NDD03N60Z−1G
IPAK
CASE 369D



NDD03N60ZT4G
DPAK
CASE 369AA

MARKING AND ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

THERMAL RESISTANCE

Parameter		Symbol	Value	Unit
Junction−to−Case (Drain)	NDF03N60Z NDD03N60Z	$R_{\theta JC}$	4.7 2.0	°C/W
Junction−to−Ambient Steady State	(Note 3) NDF03N60Z (Note 4) NDD03N60Z (Note 3) NDD03N60Z−1	$R_{\theta JA}$	51 40 80	

3. Insertion mounted
4. Surface mounted on FR4 board using 1″ sq. pad size, (Cu area = 1.127 in sq [2 oz] including traces).

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Test Conditions		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA		BV_{DSS}	600			V
Breakdown Voltage Temperature Coefficient	Reference to 25°C, I_D = 1 mA		$\Delta BV_{DSS}/\Delta T_J$		0.6		V/°C
Drain−to−Source Leakage Current	V_{DS} = 600 V, V_{GS} = 0 V	25°C	I_{DSS}			1	μA
		150°C				50	
Gate−to−Source Forward Leakage	V_{GS} = ±20 V		I_{GSS}			±10	μA
ON CHARACTERISTICS (Note 5)							
Static Drain−to−Source On−Resistance	V_{GS} = 10 V, I_D = 1.2 A		$R_{DS(on)}$		3.3	3.6	Ω
Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 50 μA		$V_{GS(th)}$	3.0	3.9	4.5	V
Forward Transconductance	V_{DS} = 15 V, I_D = 1.5 A		g_{FS}		2.0		S
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 6)	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz		C_{iss}	248	312	372	pF
Output Capacitance (Note 6)			C_{oss}	30	39	50	
Reverse Transfer Capacitance (Note 6)			C_{rss}	4	8	12	
Total Gate Charge (Note 6)	V_{DD} = 300 V, I_D = 3.0 A, V_{GS} = 10 V		Q_g	6	12	18	nC
Gate−to−Source Charge (Note 6)			Q_{gs}	1.5	2.5	4	
Gate−to−Drain (“Miller”) Charge (Note 6)			Q_{gd}	3	6.1	9	
Plateau Voltage			V_{GP}		6.4		V
Gate Resistance			R_g		6.0		Ω
RESISTIVE SWITCHING CHARACTERISTICS							
Turn−On Delay Time	V_{DD} = 300 V, I_D = 3.0 A, V_{GS} = 10 V, R_G = 5 Ω		$t_{d(on)}$		9		ns
Rise Time			t_r		8		
Turn−Off Delay Time			$t_{d(off)}$		16		
Fall Time			t_f		10		
SOURCE−DRAIN DIODE CHARACTERISTICS (T_C = 25°C unless otherwise noted)							
Diode Forward Voltage	I_S = 3.0 A, V_{GS} = 0 V		V_{SD}			1.6	V
Reverse Recovery Time	V_{GS} = 0 V, V_{DD} = 30 V, I_S = 3.0 A, di/dt = 100 A/μs		t_{rr}		265		ns
Reverse Recovery Charge			Q_{rr}		0.9		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.
6. Guaranteed by design.

TYPICAL CHARACTERISTICS

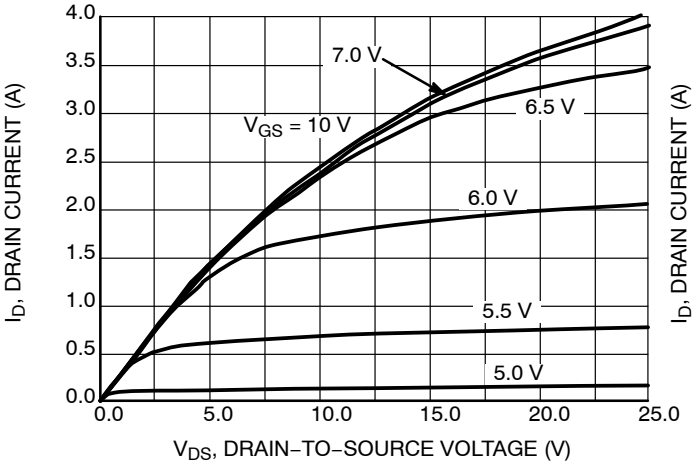


Figure 1. On−Region Characteristics

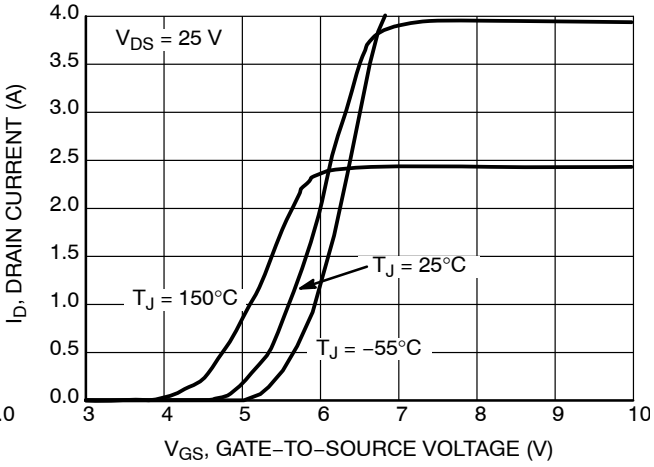


Figure 2. Transfer Characteristics

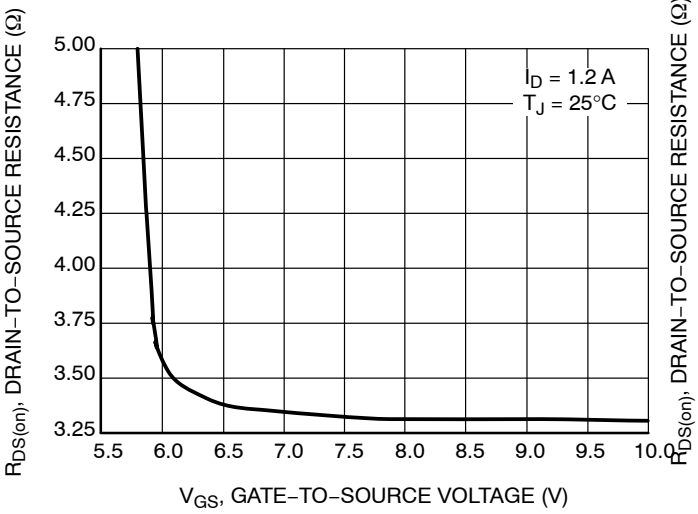


Figure 3. On−Region versus Gate−to−Source Voltage

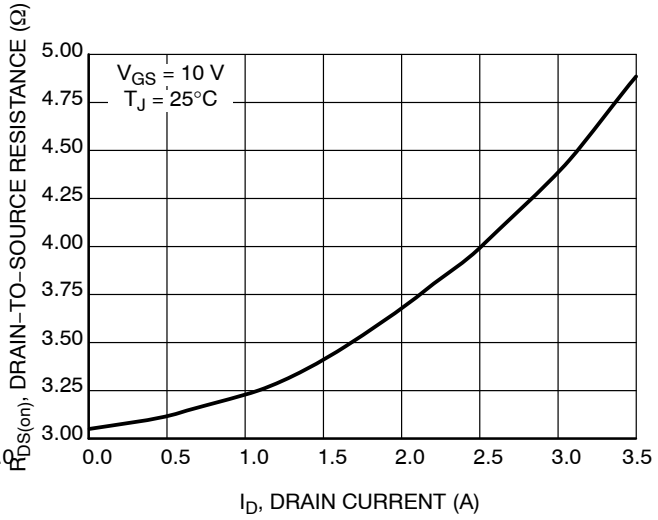


Figure 4. On−Resistance versus Drain Current and Gate Voltage

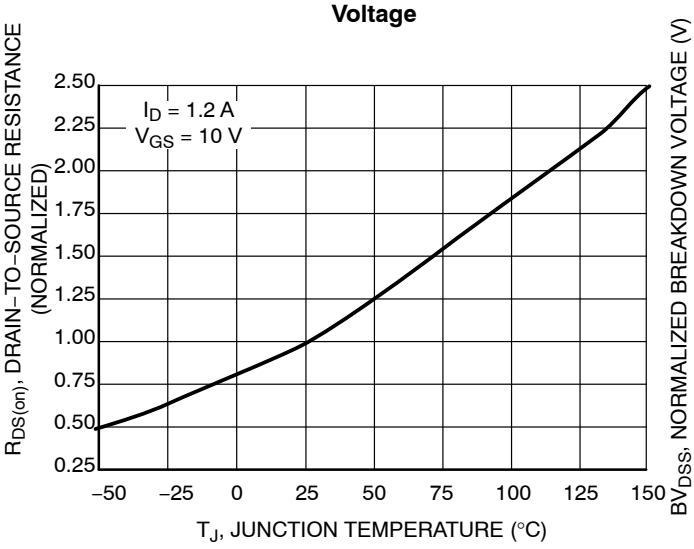


Figure 5. On−Resistance Variation with Temperature

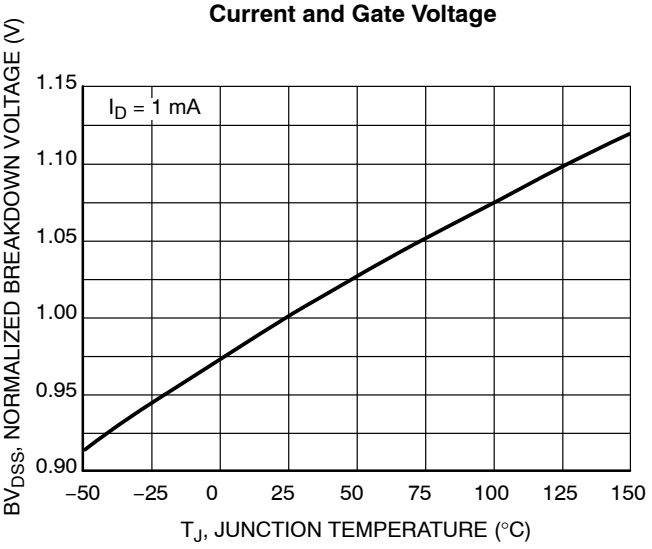


Figure 6. BV_{DSS} Variation with Temperature

TYPICAL CHARACTERISTICS

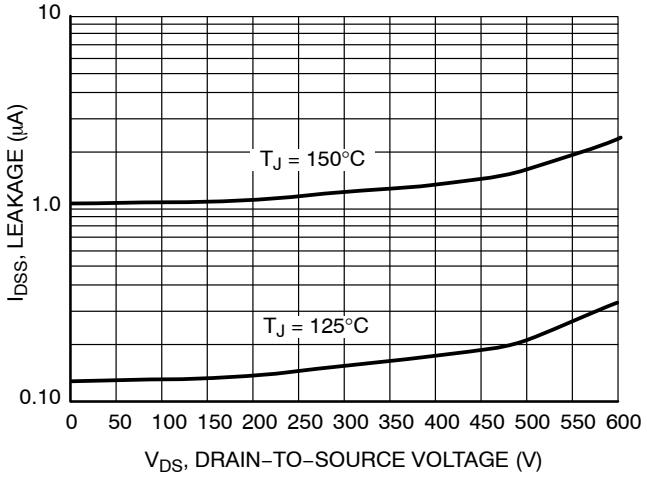


Figure 7. Drain−to−Source Leakage Current versus Voltage

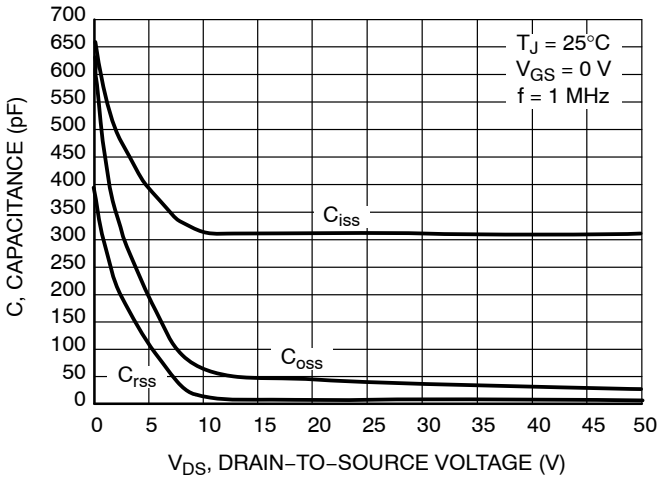


Figure 8. Capacitance Variation

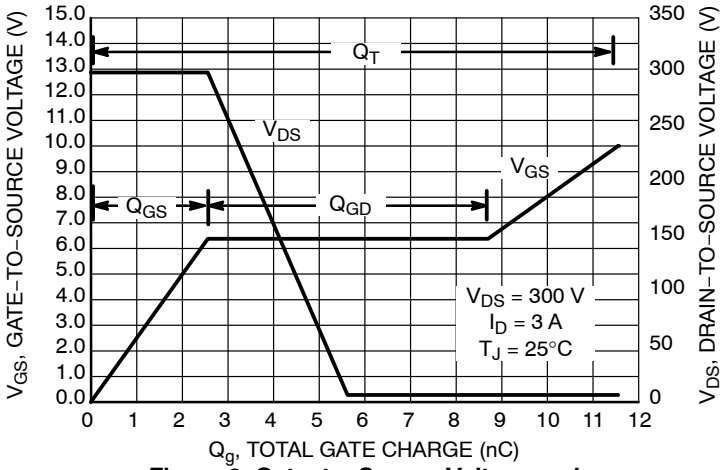


Figure 9. Gate−to−Source Voltage and Drain−to−Source Voltage versus Total Charge

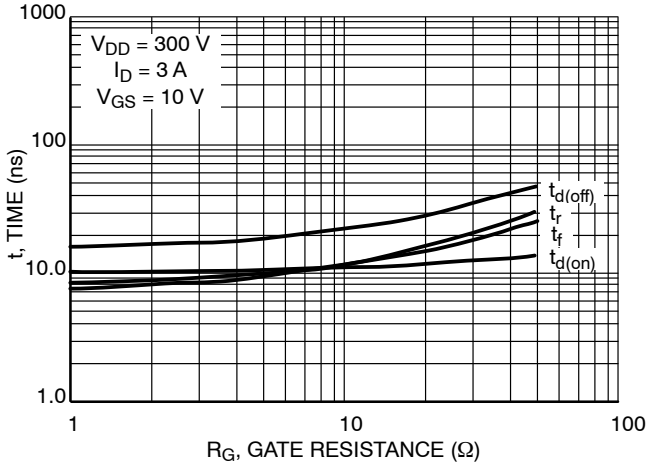


Figure 10. Resistive Switching Time Variation versus Gate Resistance

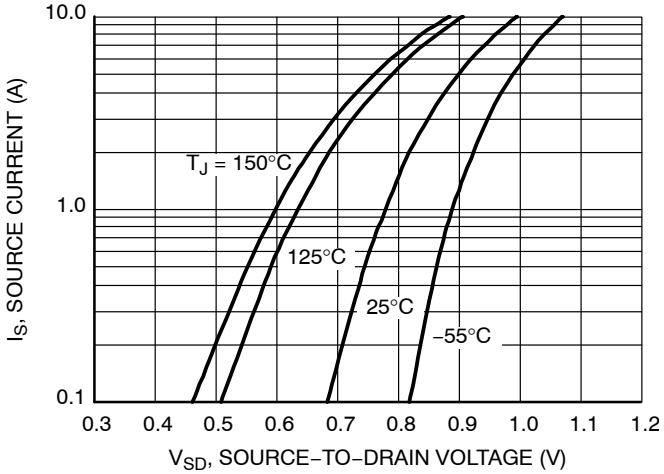


Figure 11. Diode Forward Voltage versus Current

TYPICAL CHARACTERISTICS

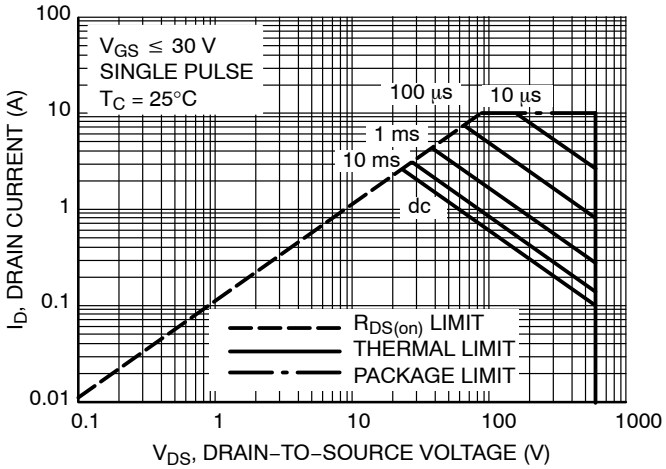


Figure 12. Maximum Rated Forward Biased Safe Operating Area NDD03N60Z

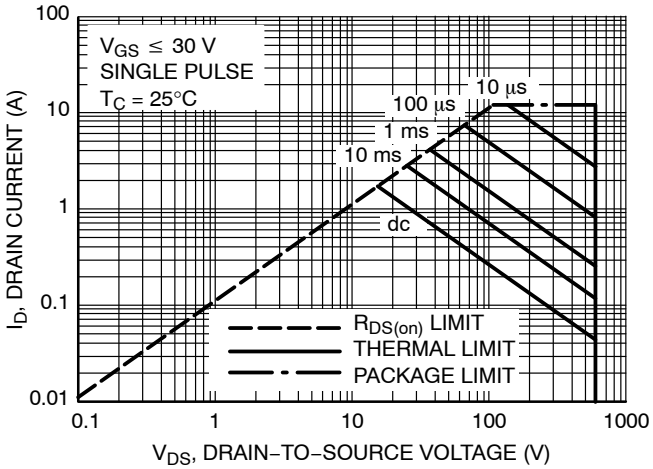


Figure 13. Maximum Rated Forward Biased Safe Operating Area NDF03N60Z

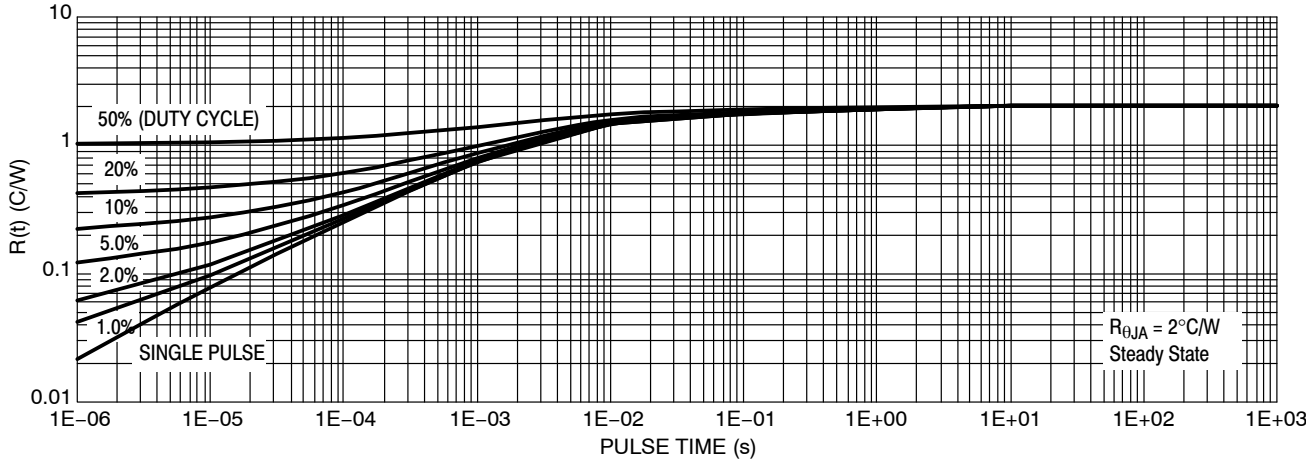


Figure 14. Thermal Impedance (Junction−to−Case) for NDD03N60Z

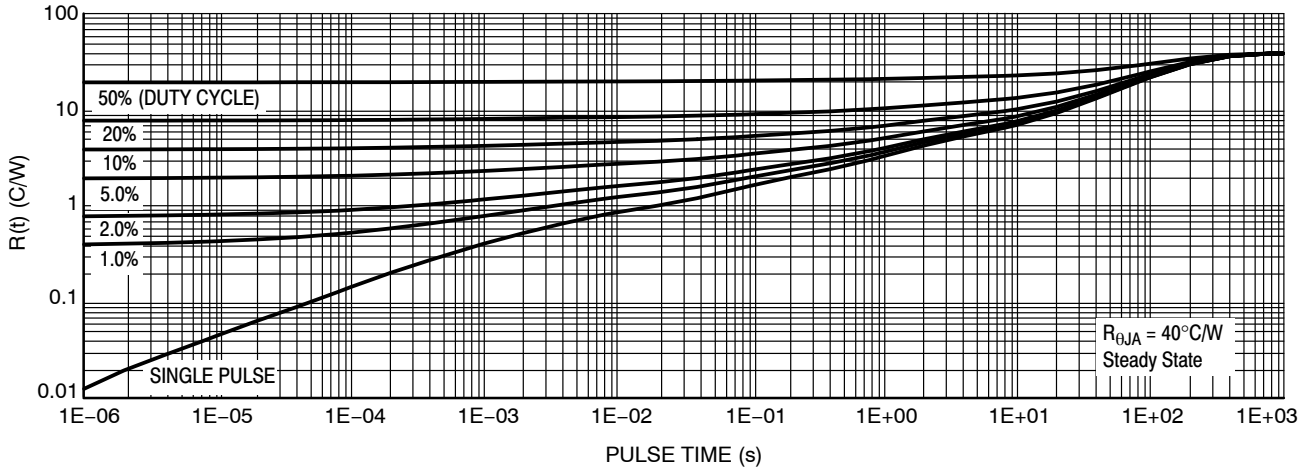


Figure 15. Thermal Impedance (Junction−to−Ambient) for NDD03N60Z

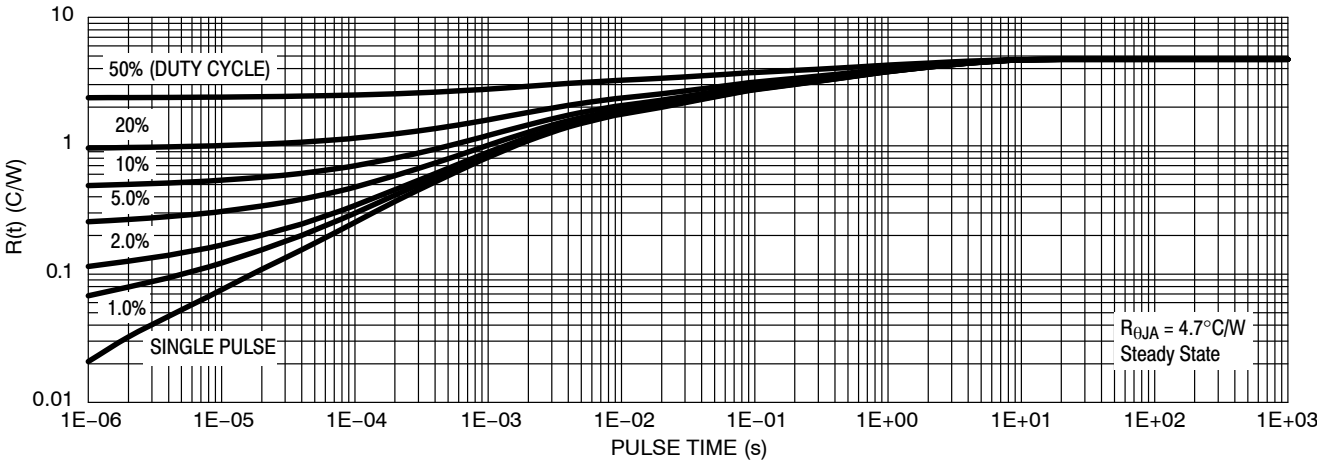


Figure 16. Thermal Impedance (Junction−to−Case) for NDF03N60Z

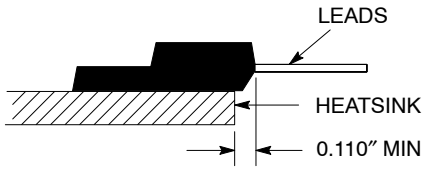


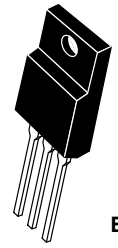
Figure 17. Isolation Test Diagram

Measurement made between leads and heatsink with all leads shorted together.

*For additional mounting information, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

TO−220 FULLPACK, 3−LEAD
CASE 221AH
ISSUE F

DATE 30 SEP 2014



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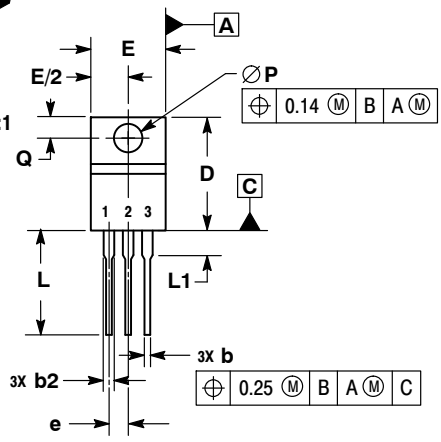
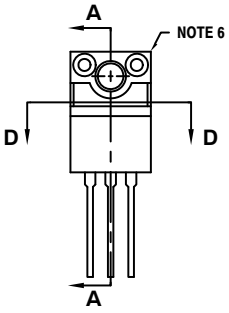
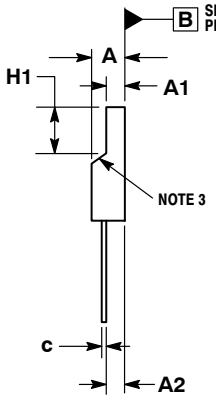


FRONT VIEW

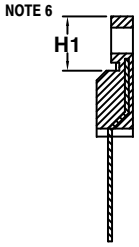
SECTION D−D



ALTERNATE CONSTRUCTION



SIDE VIEW

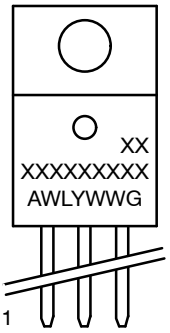


SECTION A−A

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

	MILLIMETERS	
DIM	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

GENERIC MARKING DIAGRAM*



A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

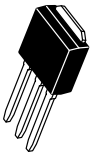
STYLE 1:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE

STYLE 2:
PIN 1. CATHODE
2. ANODE
3. GATE

DOCUMENT NUMBER:	**98AON52577E**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**TO−220 FULLPACK, 3−LEAD**	**PAGE 1 OF 1**

IPAK
CASE 369D–01
ISSUE C

DATE 15 DEC 2010



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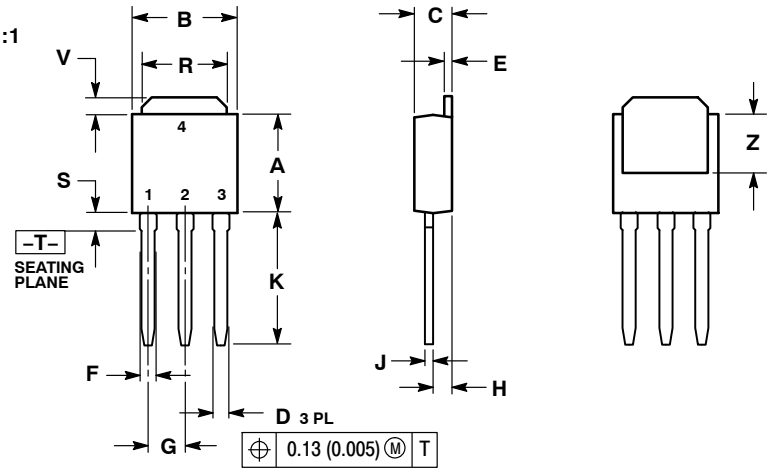


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

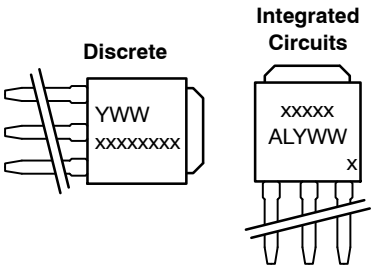
STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

MARKING DIAGRAMS

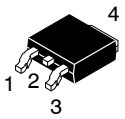


xxxxxxxxx = Device Code
A = Assembly Location
IL = Wafer Lot
Y = Year
WW = Work Week

DOCUMENT NUMBER:	98AON10528D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	IPAK (DPAK INSERTION MOUNT)	PAGE 1 OF 1

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

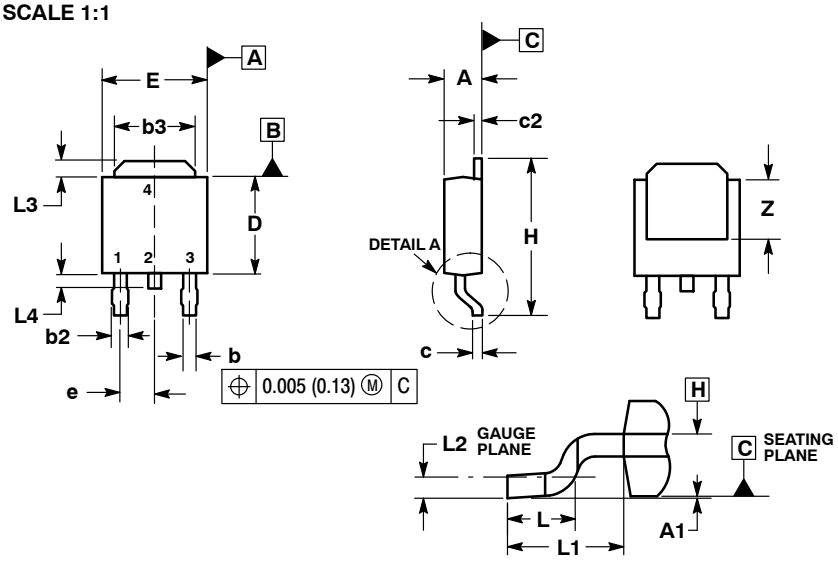
ON Semiconductor®



SCALE 1:1

DPAK (SINGLE GUAGE)
CASE 369AA−01
ISSUE B

DATE 03 JUN 2010



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	−−−	0.040	−−−	1.01
Z	0.155	−−−	3.93	−−−

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

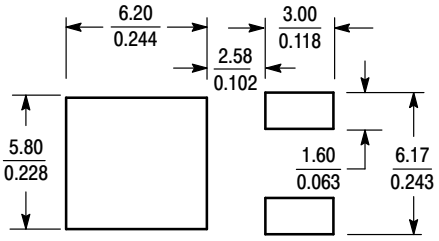
STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

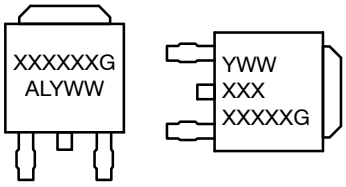
SOLDERING FOOTPRINT*



SCALE 3:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



IC Discrete

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

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